

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MRF604** is Designed for
General Purpose Oscillator
Applications up to 175 MHz.

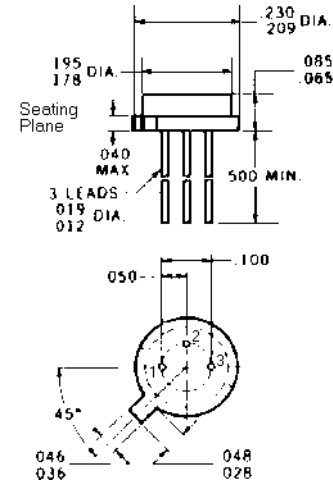
FEATURES:

- $V_{CC} = 12.5 \text{ V}$
- $P_{OUT} = 1.0 \text{ W}$
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	150 mA
V_{CB}	40 V
P_{DISS}	2.0 W @ $T_C = 25^\circ \text{C}$
T_J	-65°C to $+200^\circ \text{C}$
T_{STG}	-65°C to $+200^\circ \text{C}$
θ_{JC}	88 $^\circ \text{C/W}$

PACKAGE STYLE TO-46



CHARACTERISTICS $T_C = 25^\circ \text{C}$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 5.0 \text{ mA}$			20			V
BV_{CBO}	$I_C = 100 \mu\text{A}$			40			V
BV_{EBO}	$I_E = 100 \mu\text{A}$			3.5			V
I_{CEO}	$V_{CE} = 12 \text{ V}$					1.0	mA
h_{FE}	$V_{CE} = 5.0 \text{ V}$	$I_C = 50 \text{ mA}$		20		200	---
C_{OB}	$V_{CB} = 12.5 \text{ V}$	$f = 1.0 \text{ MHz}$				3.5	pF
η_c	$V_{CC} = 12.5 \text{ V}$	$P_{OUT} = 1.0 \text{ W}$	$f = 175 \text{ MHz}$	50			%
P_G	$V_{CC} = 12.5 \text{ V}$	$P_{OUT} = 1.0 \text{ W}$	$f = 175 \text{ MHz}$	10			dB
f_t	$V_{CE} = 10 \text{ V}$	$I_E = 50 \text{ mA}$	$f = 200 \text{ MHz}$	800			MHz